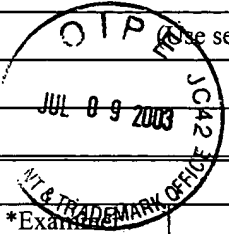


U.S. Department of Commerce, Patent and Trademark				Atty. Docket No.		Application No.		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				SNDK.256US0		10/052,924		
				Applicant(s)				
(Use several sheets if necessary)				Mokhlesi et al.				
				Filing Date		Group		
				January 18, 2002		2818		
U.S. Patent Documents								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
HU	1	4,630,086	12/16/86	Sato et al.				
	2	5,172,338	12/15/92	Mehrotra et al.				
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U.S. Published Patent Application Documents								
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		Document	Date	Country	Class	Subclass	Yes	No
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)								
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Examiner Huan HoangDate Considered 8/7/03

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.